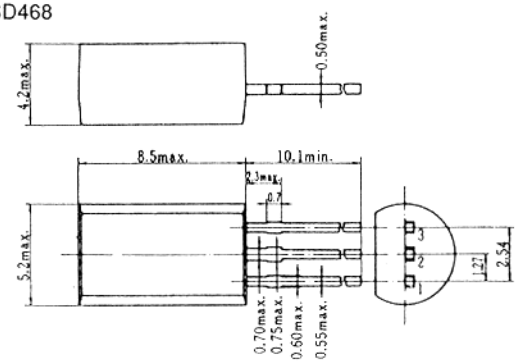
HITACHI

2SB562

SILICON PNP EPITAXIAL

LOW FREQUENCY POWER AMPLIFIER
Complementary pair with 2SD468



1. Emitter
2. Collector
3. Base

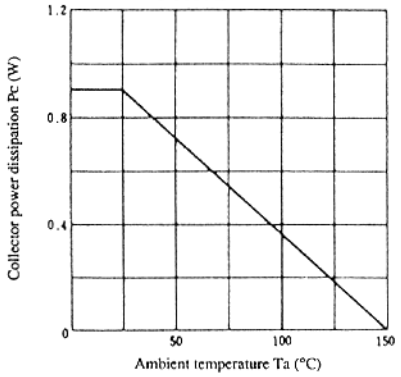
(Dimensions in mm)

(JEDEC TO-92 MOD.)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB562	Unit
Collector to base voltage	V_{CBO}	–25	V
Collector to emitter voltage	V_{CEO}	–20	V
Emitter to base voltage	V_{EBO}	–5	V
Collector current	I_C	–1.0	A
Collector peak current	$i_{C(peak)}$	–1.5	A
Collector power dissipation	P_C	0.9	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

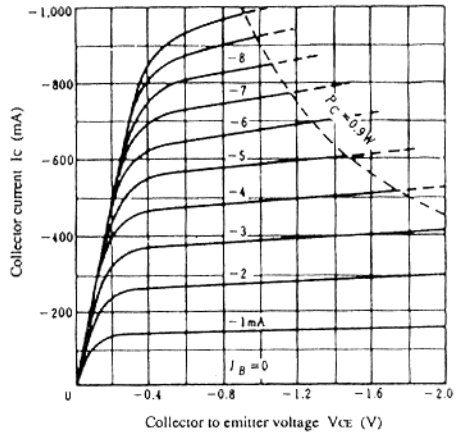
Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = –10μA, I_E = 0	–25	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = –1mA, R_{BE} = ∞	–20	—	—	V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = –10μA, I_C = 0	–5	—	—	V
Collector cutoff current	I_{CBO}	V_{CB} = –20V, I_E = 0	—	—	–1.0	μA
DC current transfer ratio	h_{FE}*	V_{CE} = –2V, I_C = –0.5A(Pulse Test)	85	—	240	
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = –0.8A, I_B = –0.08A(Pulse Test)	—	–0.2	–0.5	V
Base to emitter voltage	V_{BE}	V_{CE} = –2V, I_C = –0.5A(Pulse Test)	—	–0.8	–1.0	V
Gain bandwidth product	f_T	V_{CE} = –2V, I_C = –0.5A(Pulse Test)	—	350	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = –10V, I_E = 0, f = 1MHz	—	38	—	pF

* The 2SB562 is grouped by h_{FE} as follows.

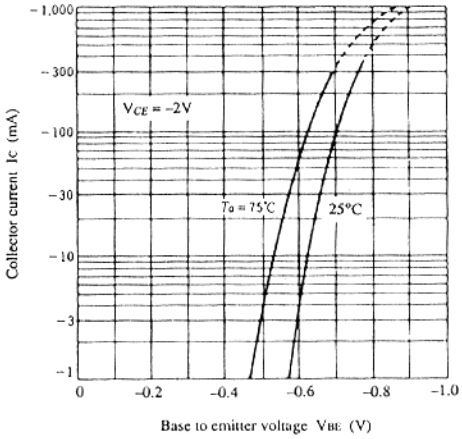
B	C
85 to 170	120 to 240

2SB562

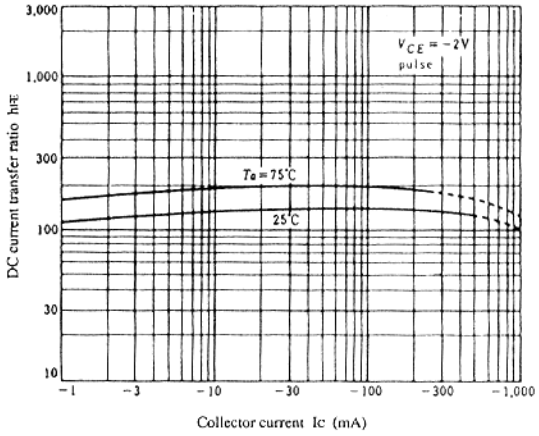
TYPICAL OUTPUT CHARACTERISTICS



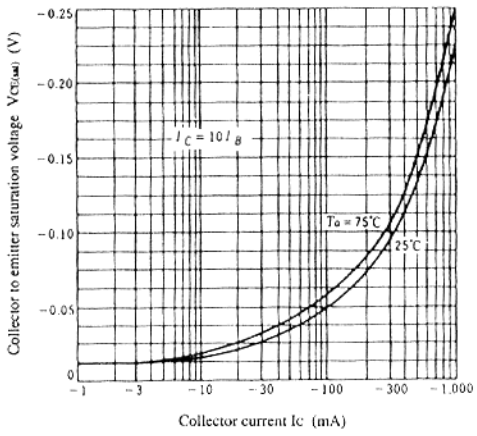
TYPICAL TRANSFER CHARACTERISTICS



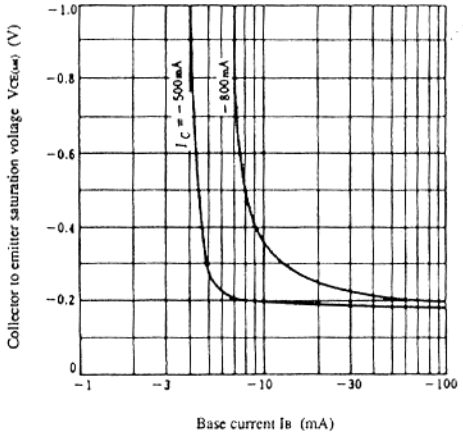
DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT



COLLECTOR TO EMITTER SATURATION VOLTAGE VS. BASE CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE